

FDD1600N10ALZD

BoostPak (N-Channel PowerTrench® MOSFET + Diode)

100 V, 6.8 A, 160 mΩ

Features

- $R_{DS(on)} = 124 \text{ m}\Omega$ (Typ.) @ $V_{GS} = 10 \text{ V}$, $I_D = 3.4 \text{ A}$
- $R_{DS(on)} = 175 \text{ m}\Omega$ (Typ.) @ $V_{GS} = 5.0 \text{ V}$, $I_D = 2.1 \text{ A}$
- Low Gate Charge (Typ. 2.78 nC)
- Low C_{rSS} (Typ. 2.04 pF)
- Fast Switching
- 100% Avalanche Tested
- Improved dv/dt Capability
- RoHS Compliant

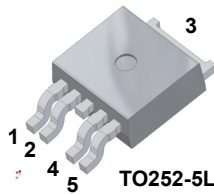
Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's PowerTrench® process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

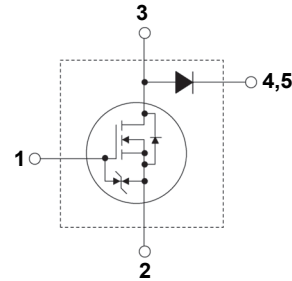
The NP diode is hyperfast rectifier with low forward voltage drop and excellent switching performance.

Applications

- LED Monitor Backlight
- LED TV Backlight
- LED Lighting
- Consumer Appliances, DC-DC converter (Step up & Step down)



1. Gate
2. Source
3. Drain / Anode
4. Cathode
5. Cathode



Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	FDD1600N10ALZD	Unit
V_{DSS}	Drain to Source Voltage	100	V
V_{GSS}	Gate to Source Voltage	± 20	V
I_D	Drain Current	- Continuous ($T_C = 25^\circ\text{C}$)	6.8
		- Continuous ($T_C = 100^\circ\text{C}$)	4.3
I_{DM}	Drain Current	- Pulsed (Note 1)	13.6
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	5.08
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	6.0
P_D	Power Dissipation	($T_C = 25^\circ\text{C}$)	14.9
		- Derate Above 25°C	0.12
I_F	Diode Continuous Forward Current ($T_C = 124^\circ\text{C}$)	4	A
I_{FM}	Diode Maximum Forward Current	40	A
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	FDD1600N10ALZD	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case for MOSFET, Max.	8.4	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case for Diode, Max.	3.3	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	87	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDD1600N10ALZD	1600N10ALZD	TO-252 5L	Tape and Reel	13"	16 mm	2500 units

Electrical Characteristics of the MOSFET $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu\text{A}, V_{GS} = 0 \text{ V}$	100	-	-	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, Referenced to 25°C	-	0.1	-	$\text{V}/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_C = 125^\circ\text{C}$	-	-	1 500	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	± 10	μA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu\text{A}$	1.4	2.1	2.8	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 3.4 \text{ A}$ $V_{GS} = 5 \text{ V}, I_D = 2.1 \text{ A}$	-	124 175	160 375	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS} = 10 \text{ V}, I_D = 6.8 \text{ A}$	-	19.6	-	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 50 \text{ V}, V_{GS} = 0 \text{ V},$ $f = 1 \text{ MHz}$	-	169	225	pF	
C_{oss}	Output Capacitance		-	43	55	pF	
C_{riss}	Reverse Transfer Capacitance		-	2.04	-	pF	
$C_{oss(er)}$	Energy Related Output Capacitance	$V_{DS} = 50 \text{ V}, V_{GS} = 0 \text{ V}$	-	85	-	pF	
$Q_{g(tot)}$	Total Gate Charge at 10V	$V_{GS} = 10 \text{ V}$	$V_{DD} = 50 \text{ V},$ $I_D = 6.8 \text{ A}$ (Note 4)	-	2.78	3.61	nC
$Q_{g(tot)}$	Total Gate Charge at 5V	$V_{GS} = 5 \text{ V}$		-	1.5	1.95	nC
Q_{gs}	Gate to Source Gate Charge			-	0.72	-	nC
Q_{gd}	Gate to Drain "Miller" Charge			-	0.56	-	nC
$V_{plateau}$	Gate Plateau Voltage			-	4.02	-	V
Q_{sync}	Total Gate Charge Sync.	$V_{DS} = 0 \text{ V}, I_D = 3.4 \text{ A}$	-	2.5	-	nC	
Q_{oss}	Output Charge	$V_{DS} = 50 \text{ V}, V_{GS} = 0 \text{ V}$	-	5.2	-	nC	

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 50 \text{ V}, I_D = 6.8 \text{ A},$ $V_{GS} = 10 \text{ V}, R_G = 4.7 \Omega$ (Note 4)	-	7	24	ns
t_r	Turn-On Rise Time		-	2	14	ns
$t_{d(off)}$	Turn-Off Delay Time		-	13	36	ns
t_f	Turn-Off Fall Time		-	2	14	ns
ESR	Equivalent Series Resistance (G-S)	$f = 1 \text{ MHz}$	-	2.1	-	Ω

Drain-Source Diode Characteristics

I_S	Maximum Continuous Drain to Source Diode Forward Current	-	-	6.8	A	
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current	-	-	13.6	A	
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{SD} = 6.8 \text{ A}$	-	-	1.3	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0 \text{ V}, I_{SD} = 6.8 \text{ A}, V_{DS} = 50 \text{ V},$ $di_F/dt = 100 \text{ A}/\mu\text{s}$	-	37	-	ns
Q_{rr}	Reverse Recovery Charge		-	42	-	nC

Notes:

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2. $L = 1 \text{ mH}, I_{AS} = 3.18 \text{ A}, R_G = 25 \Omega$, starting $T_J = 25^\circ\text{C}$.
3. $I_{SD} \leq 6.8 \text{ A}, di/dt \leq 200 \text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, starting $T_J = 25^\circ\text{C}$.
4. Essentially independent of operating temperature typical characteristics.

Electrical Characteristics of the Diode $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
V_R	DC Blocking Voltage	$I_R = 1 \text{ mA}$	150	-	-	V	
V_{FM}	Maximum Instantaneous Forward Voltage	$I_F = 4 \text{ A}$	$T_C = 25^\circ\text{C}$	-	-	2.5	V
			$T_C = 125^\circ\text{C}$	-	1.01	-	
I_{RM}	Maximum Instantaneous Reverse Current @ rated V_R		$T_C = 25^\circ\text{C}$	-	-	50	uA
			$T_C = 125^\circ\text{C}$	-	-	1000	
t_{rr}	Diode Reverse Recovery Time	$I_F = 4 \text{ A},$ $di/dt = 200 \text{ A}/\mu\text{s}$	$T_C = 25^\circ\text{C}$	-	12.7	26	ns
			$T_C = 125^\circ\text{C}$	-	17.1	-	
I_{rr}	Diode Peak Reverse Recovery Current	$I_F = 4 \text{ A},$ $di/dt = 200 \text{ A}/\mu\text{s}$	$T_C = 25^\circ\text{C}$	-	2.6	6	A
			$T_C = 125^\circ\text{C}$	-	3.8	-	
Q_{rr}	Diode Reverse Recovery Charge	$I_F = 4 \text{ A},$ $di/dt = 200 \text{ A}/\mu\text{s}$	$T_C = 25^\circ\text{C}$	-	18.3	-	nC
			$T_C = 125^\circ\text{C}$	-	35.7	-	
W_{AVL}	Avalanche Energy (L = 40 mH)		10	-	-	mJ	

Typical Performance Characteristics - MOSFET

Figure 1. On-Region Characteristics

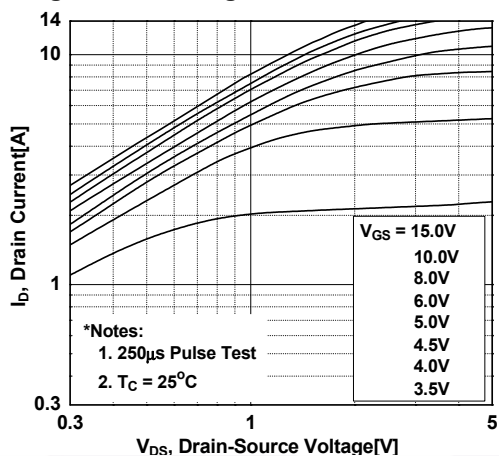


Figure 2. Transfer Characteristics

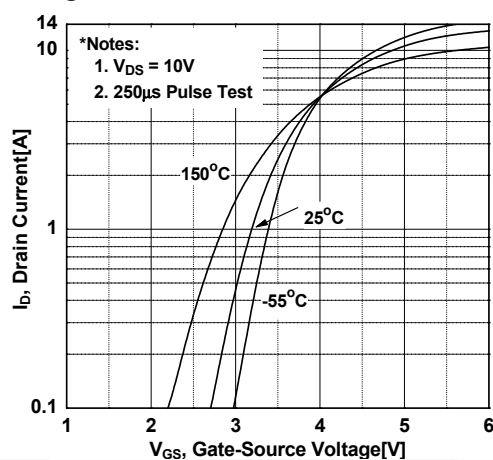


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

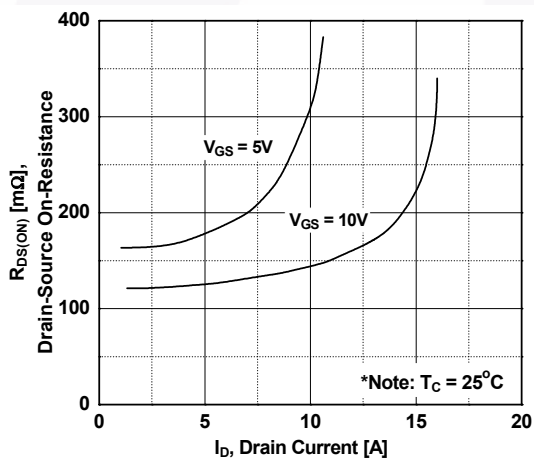


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

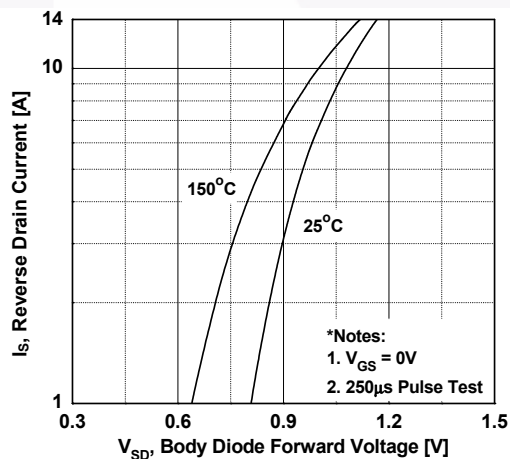


Figure 5. Capacitance Characteristics

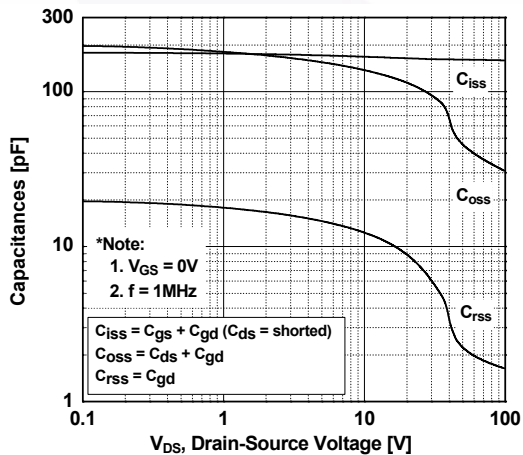
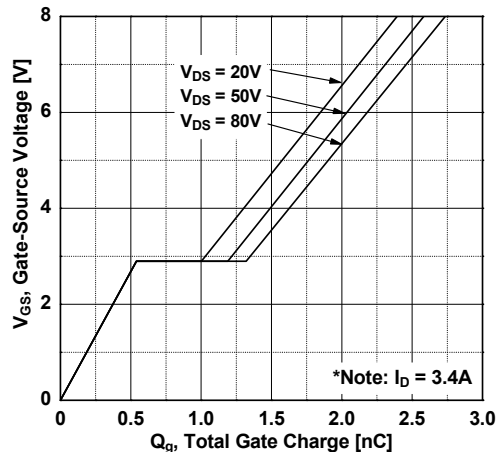


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics - MOSFET (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

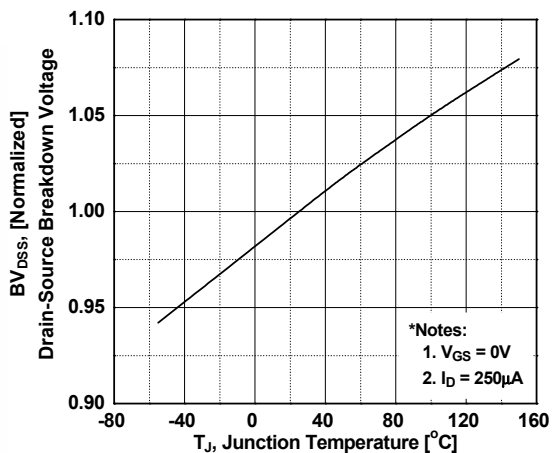


Figure 8. On-Resistance Variation vs. Temperature

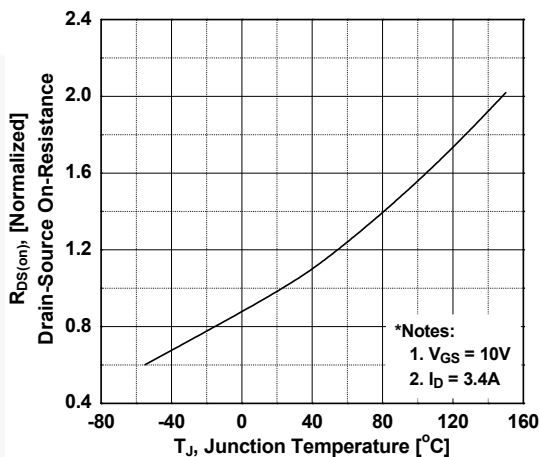


Figure 9. Maximum Safe Operating Area

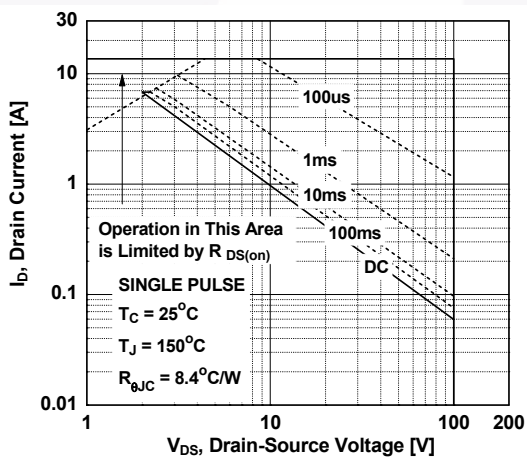


Figure 10. Maximum Drain Current vs. Case Temperature

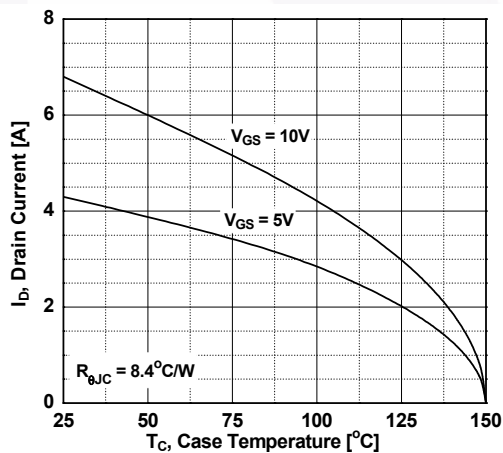


Figure 11. E_oss vs. Drain to Source Voltage

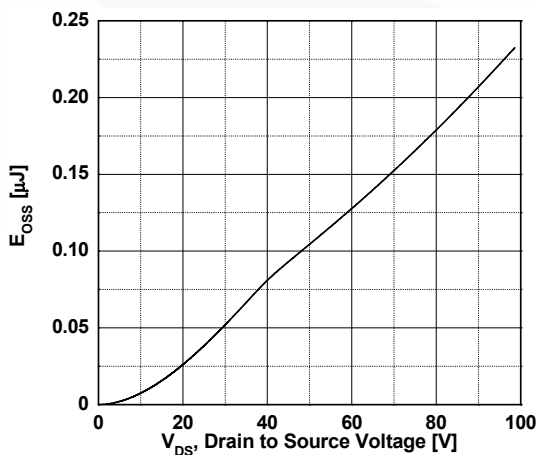
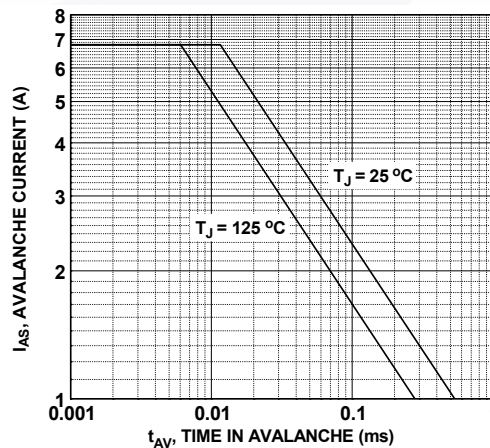


Figure 12. Unclamped Inductive Switching Capability



Typical Performance Characteristics - Diode (Continued)

Figure 13. Forward Voltage Drop vs. Forward Current

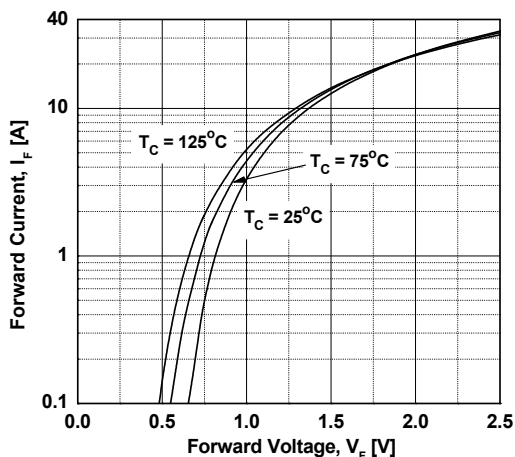


Figure 14. Reverse Current vs. Reverse Voltage

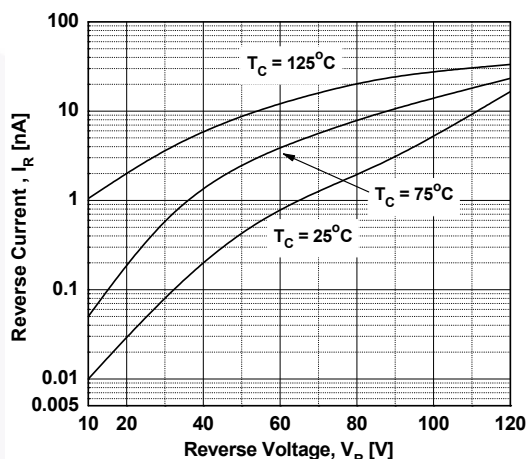


Figure 15. Junction Capacitance

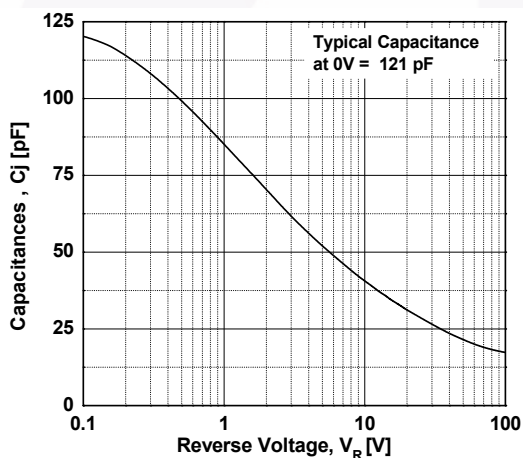


Figure 16. Reverse Recovery Time vs. di/dt

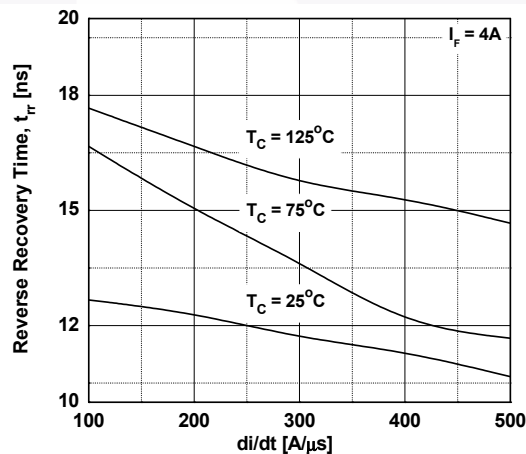


Figure 17. Reverse Recovery Current vs. di/dt

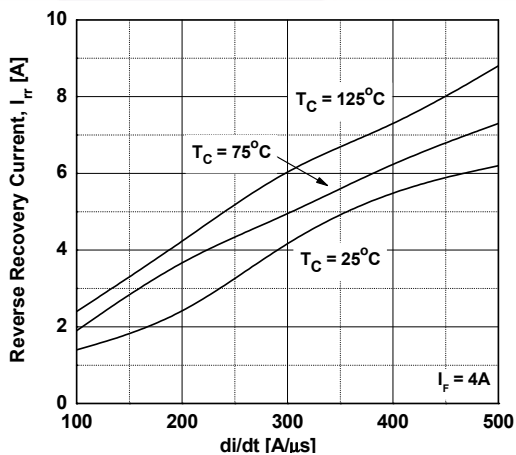
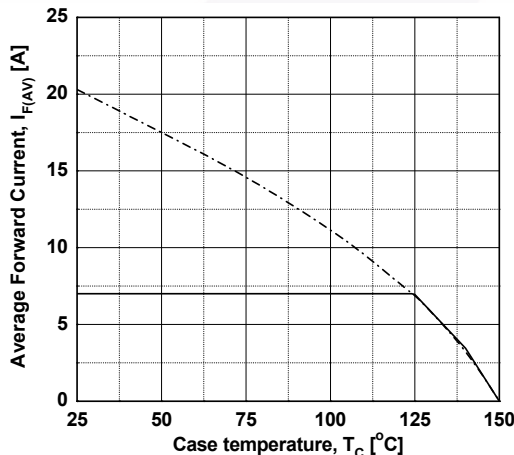


Figure 18. Forward Current Derating Curve



Typical Performance Characteristics (Continued)

Figure 19. Transient Thermal Response Curve of MOSFET

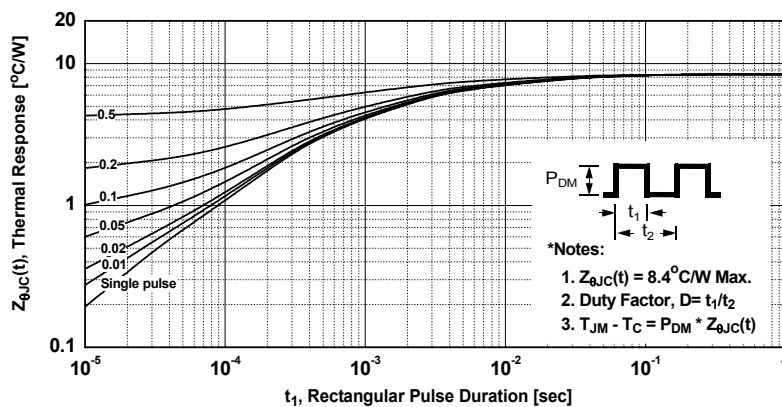
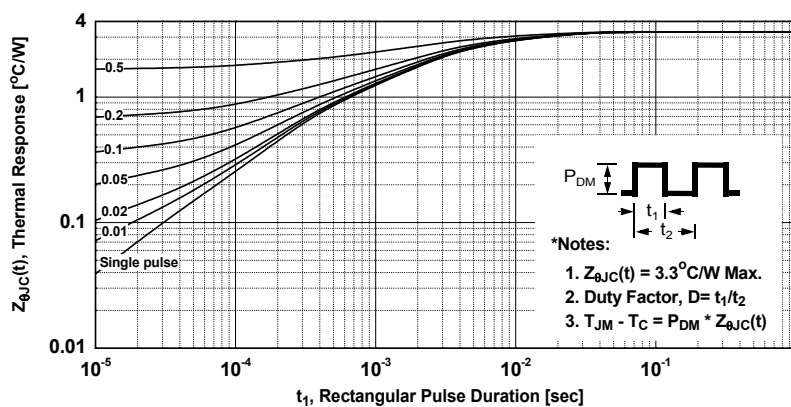


Figure 20. Transient Thermal Response Curve of Diode



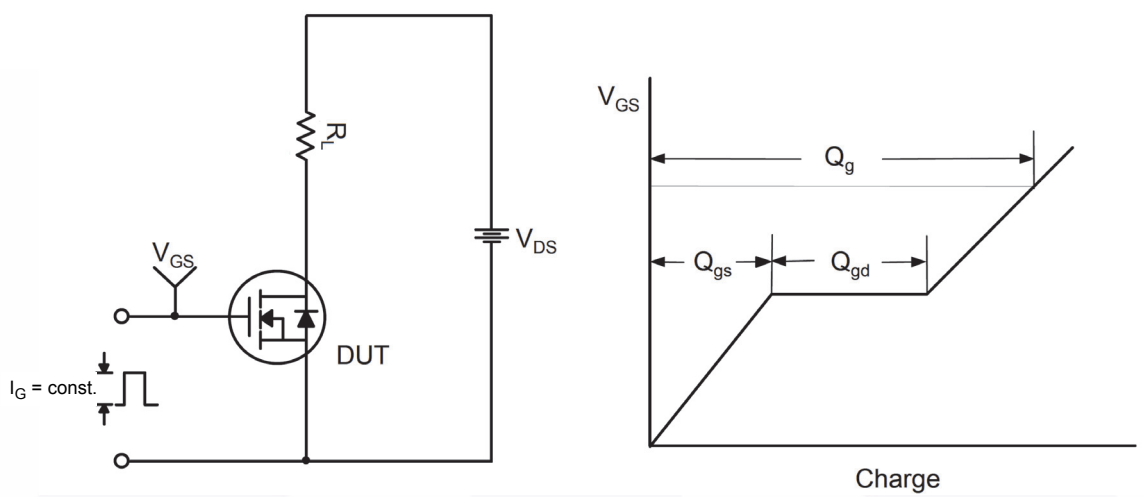


Figure 21. Gate Charge Test Circuit & Waveform

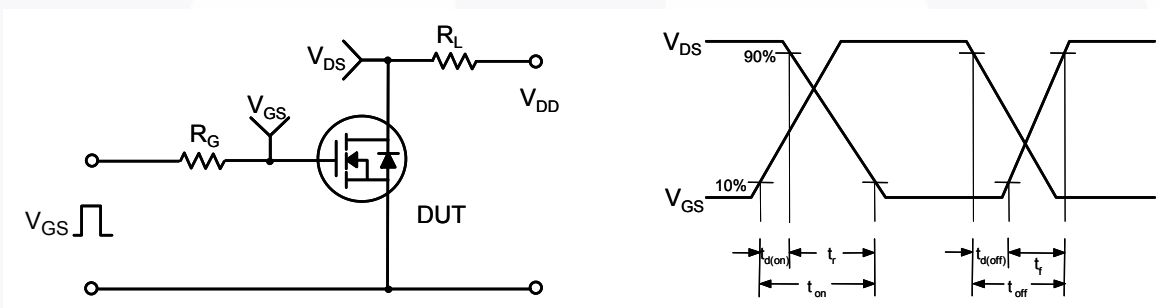


Figure 22. Resistive Switching Test Circuit & Waveforms

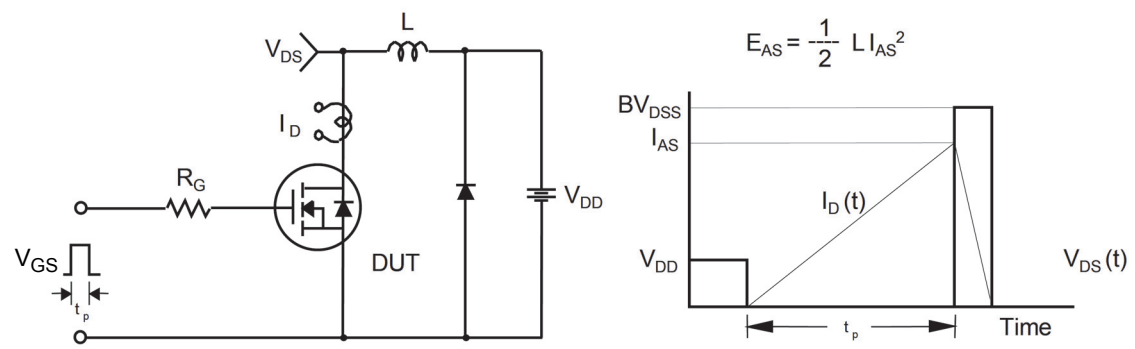


Figure 23. Unclamped Inductive Switching Test Circuit & Waveforms

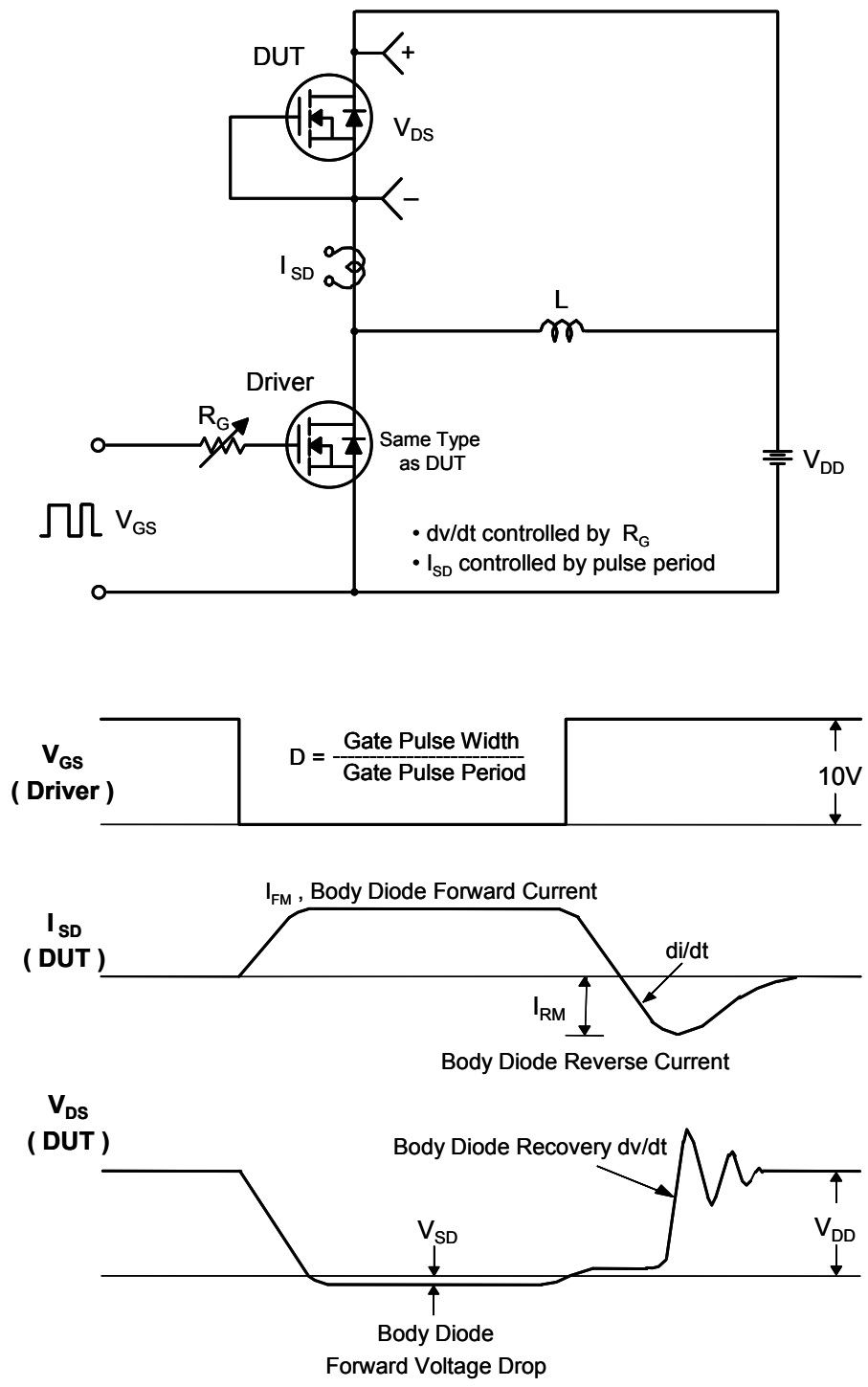


Figure 24. Peak Diode Recovery dv/dt Test Circuit & Waveforms

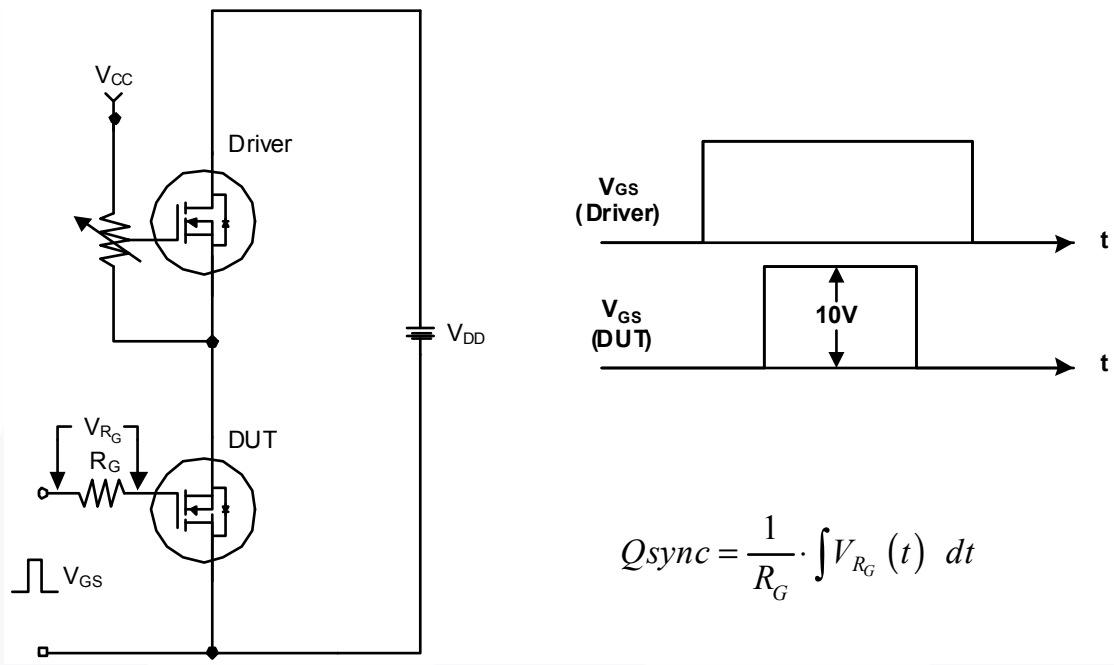


Figure 25. Total Gate Charge Q_{sync} . Test Circuit & Waveforms

